

BUK7M12-40E

N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33
19 September 2016 Product data sheet

1. General description

Standard level N-channel MOSFET in an LFPAK33 (Power33) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|------|
| V_{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | - | - | 40 | V |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | - | 48 | Α |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | - | 55 | W |
| Static chara | cteristics | | | | | |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11 | - | 9.8 | 12 | mΩ |
| Dynamic ch | aracteristics | | | | | |
| Q_{GD} | gate-drain charge | I _D = 15 A; V _{DS} = 32 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> | - | 5.4 | - | nC |



N-channel 40 V, 12 m Ω standard level MOSFET in LFPAK33

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1 | S | Source | | D I |
| 2 | S | Source | | |
| 3 | S | Source | | G T A |
| 4 | G | Gate | | mbb076 S |
| mb | D | Mounting base; connected to drain | LFPAK33 (SOT1210) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|---|---------|--|--|
| | Name | Description | Version | | |
| BUK7M12-40E | LFPAK33 | Plastic single ended surface mounted package (LFPAK33); 8 leads | SOT1210 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BUK7M12-40E | 71240E |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|
| V _{DS} | drain-source voltage | 25 °C ≤ T _j ≤ 175 °C | - | 40 | V |
| V_{DGR} | drain-gate voltage | R_{GS} = 20 k Ω | - | 40 | V |
| V _{GS} | gate-source voltage | DC; T _j ≤ 175 °C | -20 | 20 | V |
| P _{tot} | total power dissipation | T _{mb} = 25 °C; <u>Fig. 1</u> | - | 55 | W |
| I _D | drain current | V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u> | - | 48 | Α |
| | | V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u> | - | 34 | Α |
| I _{DM} | peak drain current | pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3 | - | 192 | Α |
| T _{stg} | storage temperature | | -55 | 175 | °C |

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N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|--------|-----|------|------|
| T _j | junction temperature | | | -55 | 175 | °C |
| Source-drain | diode | | | | | |
| I _S | source current | T _{mb} = 25 °C | | - | 45.5 | Α |
| I _{SM} | peak source current | pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$ | | - | 192 | Α |
| Avalanche ru | uggedness | | | | | |
| E _{DS(AL)S} | non-repetitive drain-source avalanche energy | I_D = 48 A; V_{sup} ≤ 40 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4 | [1][2] | - | 23.7 | mJ |

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.

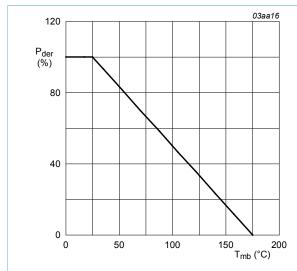
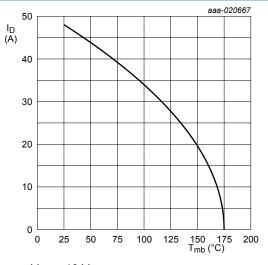


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

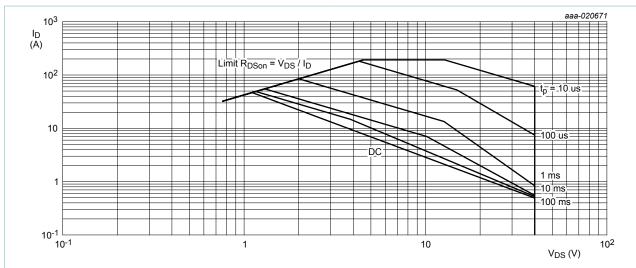


 $V_{GS} \ge 10 \text{ V}$

Fig. 2. Continuous drain current as a function of mounting base temperature

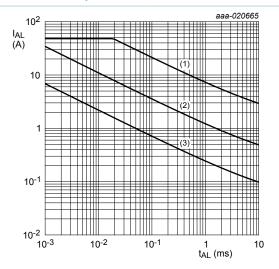
$$I_D = 48A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}} \text{ for } T_{mb} \ge 25^{\circ}C$$

N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33



 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

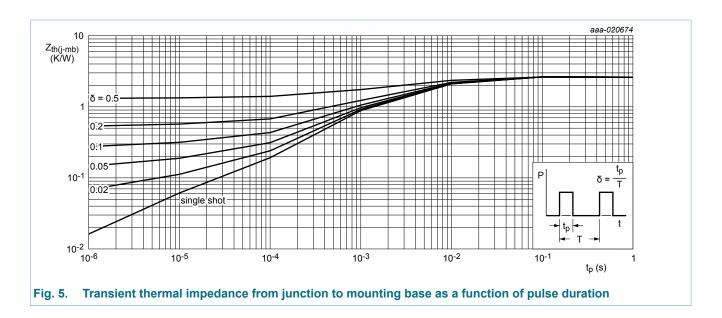
Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------------|---|------------|-----|------|------|------|
| R _{th(j-mb)} | thermal resistance from junction to mounting base | Fig. 5 | - | 2.46 | 2.75 | K/W |

BUK7M12-40E

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N-channel 40 V, 12 m Ω standard level MOSFET in LFPAK33



10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------------|----------------------------------|---|-----|------|------|------|
| Static chara | acteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$ | 40 | - | - | V |
| | breakdown voltage | $I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$ | 36 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10 | 2.4 | 3 | 4 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9 | - | - | 4.5 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9 | 1 | - | - | V |
| I _{DSS} drain leaka | drain leakage current | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C | - | 0.01 | 1 | μA |
| | | V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C | - | - | 500 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| | | V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C | - | 2 | 100 | nA |
| R _{DSon} | drain-source on-state resistance | V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 11 | - | 9.8 | 12 | mΩ |
| | | V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; Fig. 12 | - | - | 23.6 | mΩ |
| Dynamic ch | naracteristics | | | | | |
| Q _{G(tot)} | total gate charge | I _D = 15 A; V _{DS} = 32 V; V _{GS} = 10 V; | - | 15.8 | - | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u> | - | 4 | - | nC |
| Q_{GD} | gate-drain charge | 1 | - | 5.4 | - | nC |

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N-channel 40 V, 12 m Ω standard level MOSFET in LFPAK33

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|------------------------------|---|---|-----|------|-----|------|
| C _{iss} | input capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 15$ | | - | 736 | 979 | pF |
| C _{oss} | output capacitance | | | - | 155 | 186 | pF |
| C _{rss} | reverse transfer capacitance | | | - | 97 | 133 | pF |
| t _{d(on)} | turn-on delay time | $V_{DS} = 30 \text{ V}; R_{L} = 2 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_{j} = 25 \text{ °C}$ | | - | 5.2 | - | ns |
| t _r | rise time | | | - | 7 | - | ns |
| t _{d(off)} | turn-off delay time | | | - | 11.4 | - | ns |
| t _f | fall time | | | - | 6.7 | - | ns |
| Source-dra | nin diode | 1 | I | 1 | | | |
| V_{SD} | source-drain voltage | $I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$ | | - | 0.86 | 1.2 | V |
| t _{rr} | reverse recovery time | I_S = 15 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 25 V; T_j = 25 °C | | - | 17.8 | - | ns |
| Q _r | recovered charge | | | - | 11.1 | - | nC |

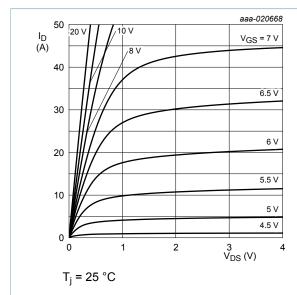


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

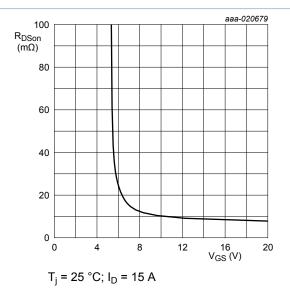


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33

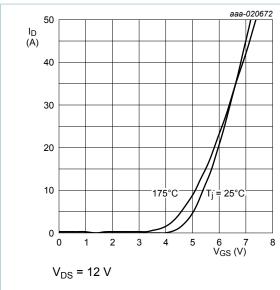


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

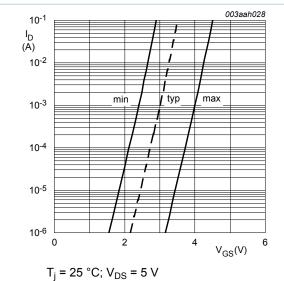


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

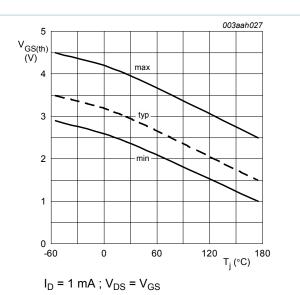


Fig. 9. Gate-source threshold voltage as a function of junction temperature

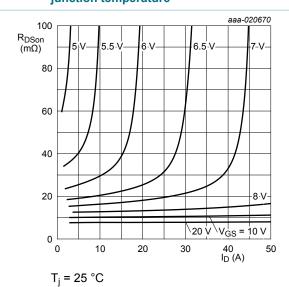


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33

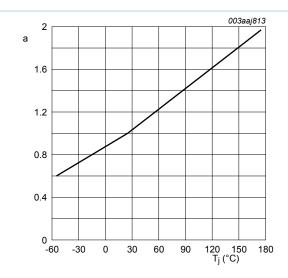


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}C)}$$

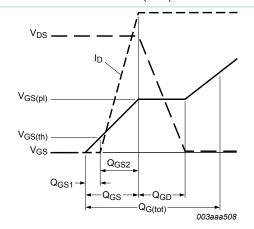
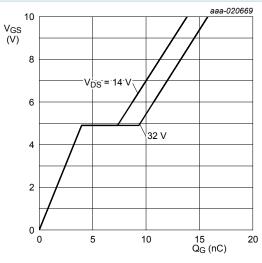
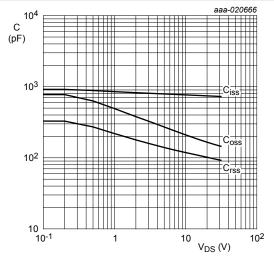


Fig. 14. Gate charge waveform definitions



 $T_i = 25 \,^{\circ}\text{C}; I_D = 15 \,\text{A}$

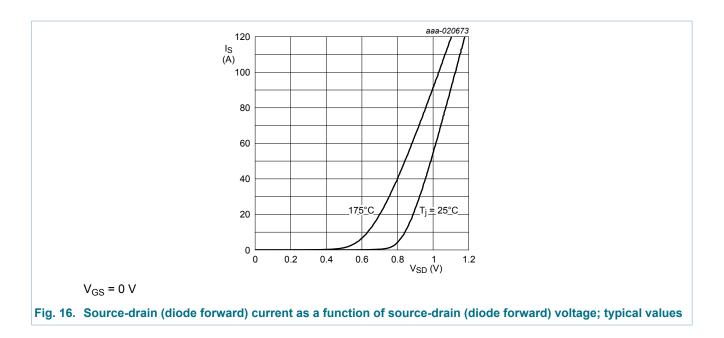
Fig. 13. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33

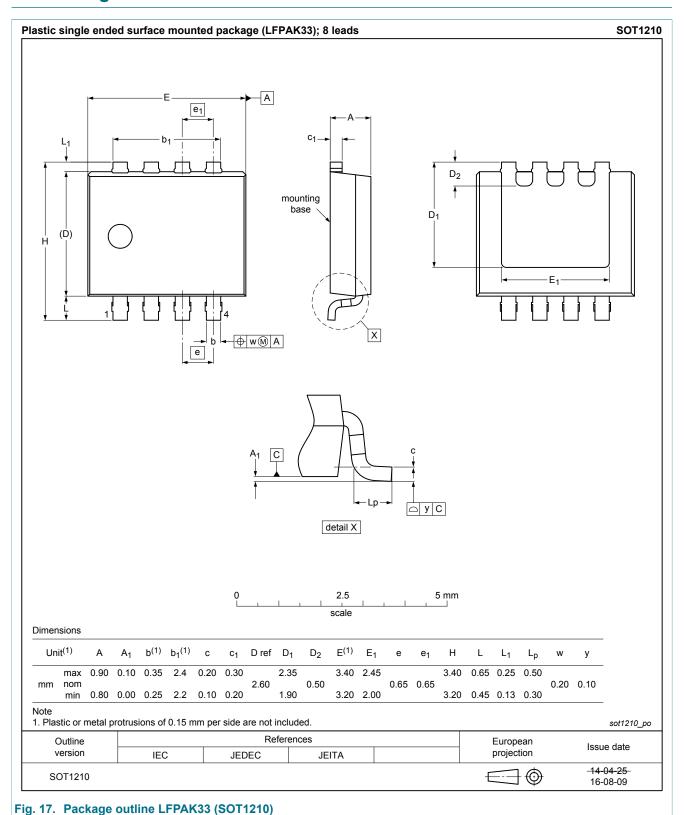


11. Application information

For guidance on how to use and understand this datasheet, please refer to application note AN11158 "Understanding power MOSFET datasheet parameters".

N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33

12. Package outline



BUK7M12-40E

N-channel 40 V, 12 mΩ standard level MOSFET in LFPAK33

13. Legal information

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|--------------------------------------|--------------------|---|
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N-channel 40 V, 12 m Ω standard level MOSFET in LFPAK33

14. Contents

| 1 | General description | 1 |
|------|-------------------------|----|
| 2 | Features and benefits | 1 |
| 3 | Applications | 1 |
| 4 | Quick reference data | 1 |
| 5 | Pinning information | 2 |
| 6 | Ordering information | |
| 7 | Marking | |
| 8 | Limiting values | 2 |
| 9 | Thermal characteristics | 4 |
| 10 | Characteristics | 5 |
| 11 | Application information | 9 |
| 12 | Package outline | 10 |
| 13 | Legal information | 11 |
| 13.1 | Data sheet status | 11 |
| 13.2 | Definitions | 11 |
| 13.3 | Disclaimers | 11 |
| 13.4 | Trademarks | 12 |
| | | |

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Product data sheet

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